

ABSTRACT OF THE DISCLOSURE

1 A surge protection device includes a gate electrode embedded in an
2 insulator, a source electrode and a drain electrode on the insulator. The
3 source and drain electrodes respectively form first and second capacitances
4 with the gate electrode. A semiconductor island is provided on the insulator
5 to form a channel between the source and drain electrodes and a third
6 capacitance with the gate electrode. The third capacitance is smaller than
7 either of the first and second capacitances. The source and drain electrodes
8 are adapted for connection to external circuitry for establishing a low-
9 impedance path when the external circuitry is subjected to a surge potential.

100-1044-1